

Silicon N-Channel Junction FET

Description

Making the best of Epitaxy and Pattern latest technology, 2SK300 accomplishes so far unattainable levels of performance.

Usage with head amplifiers for video cameras and the like, ensures the highest efficiency.

Features

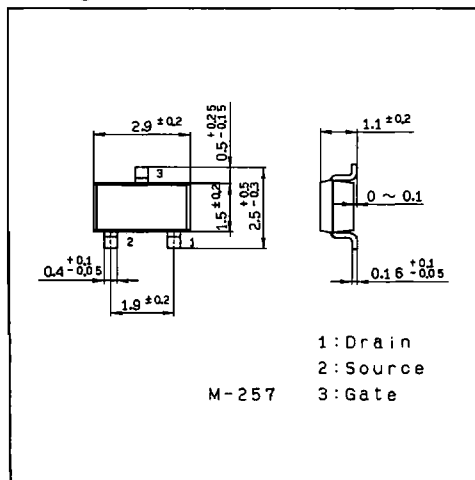
- High figure of merit
 $V_{DS}=5V$ |Yfs|/Ciss 3.5 (Typ.)
 $I_D=10mA$
- High |Yfs|
 $V_{DS}=5V$ |Yfs| 30mS (Typ.)
 $V_{GS}=0V$
- Low input capacitance
 Ciss 8pF (Typ.)

Absolute Maximum Ratings (Ta=25°C)

- Drain to gate voltage V_{DGO} 15 V
- Source to gate voltage V_{SGO} 15 V
- Drain current I_D 50 mA
- Gate current I_G 5 mA
- Junction temperature T_J 150 °C
- Storage temperature T_{stg} -55 to +150 °C
- Allowable power dissipation P_D 150 mW

Package Outline

Unit : mm



Structure

Silicon N-Channel junction FET

Electrical Characteristics

(Ta=25°C)

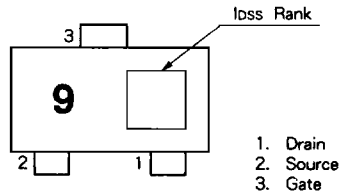
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to gate voltage	V_{DGO}	$I_G=10 \mu A$	15			V
Source to gate voltage	V_{SGO}	$I_G=10 \mu A$	15			V
Gate cutoff current	I_{GSS}	$V_{GS}=-7V, V_{DS}=0V$			-2	nA
Drain current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	9.5		42	mA *
Gate to source cutoff voltage	$V_{GS(OFF)}$	$V_{DS}=5V, I_D=100 \mu A$	-0.55		-2.0	V
Forward transfer admittance	Yfs	$V_{DS}=5V, V_{GS}=0V, f=1kHz$	21	30		mS
Input capacitance	Ciss	$V_{DS}=5V, V_{GS}=0V, f=1MHz$		8	9	pF

* Drain current detail specification as follows.

Classification ($V_{ds}=5V, V_{gs}=0V$)

Rank	I_{dss} (mA)
1	9.5 to 14.8
2	13.4 to 21.0
3	19.0 to 30.2
4	27.4 to 42.0
3/4 *	19.0 to 42.0

Mark



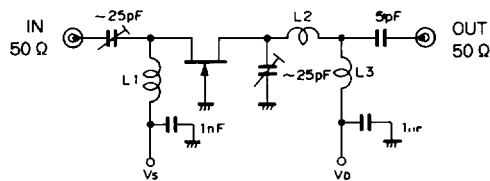
* Rank 3 or 4 is indicated on I_{dss} rank of Rank 3/4.

Standard Circuit Design Data

($T_a=25^\circ C$)

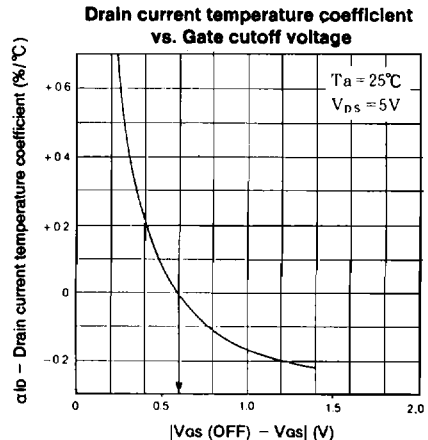
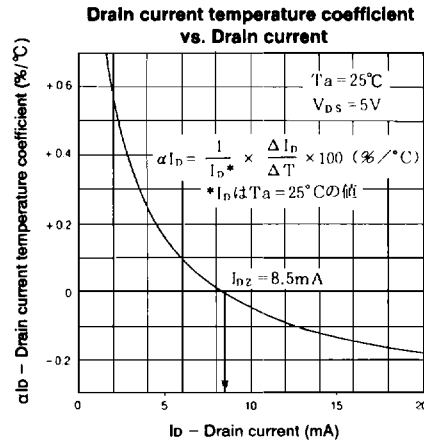
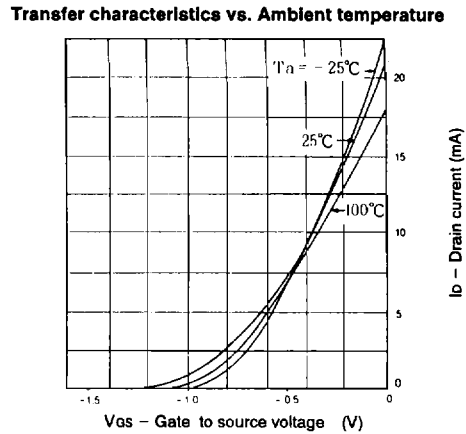
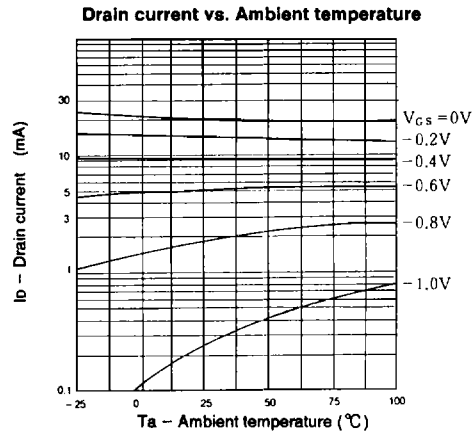
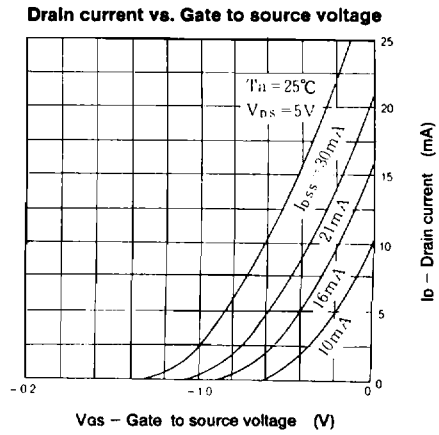
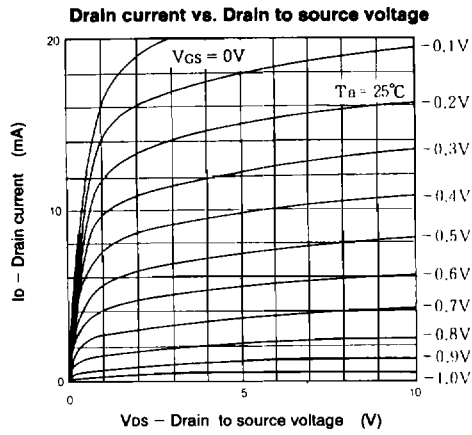
Item	Symbol	Condition	Typ.	Unit
Forward transfer admittance	$ Y_{fs} $	$V_{ds}=5V, I_b=10mA, f=1kHz$	25	mS
Input capacitance	C_{iss}	$V_{ds}=5V, I_b=10mA, f=1MHz$	7.2	pF
Gate cutoff current	I_g	$V_{ds}=5V, I_b=10mA$	40	pA
Input resistance	r_{is}	$V_{ds}=5V, I_b=10mA, f=100MHz$	3.5	k Ω
Input capacitance	C_{is}		7.2	pF
Output resistance	r_{os}		3	k Ω
Output capacitance	C_{os}		2.5	pF
Power gain	PG		15	dB
Noise figure	NF	1.8	dB	
Equivalent input noise voltage	\bar{e}_n	$V_{ds}=5V, I_b=10mA, f=1kHz, R_g=0\Omega$	1.2	nV/\sqrt{Hz}
Reverse transfer capacitance	C_{rss}	$V_{ds}=5V, V_{gs}=0V, f=1MHz$	2.0	pF

100MHz PG, NF Test Circuit

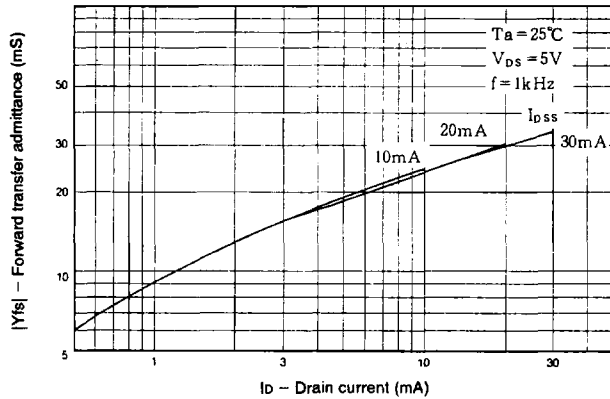


- L1 } ϕ 0.45mm Polyurethane Wire ϕ 3mm 10.5t
- L2 } ϕ 0.45mm Polyurethane Wire ϕ 3mm 5.5t
- L3 }

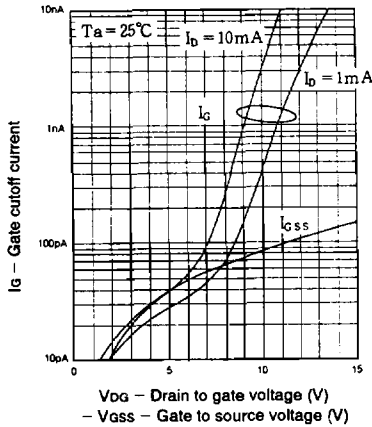
Example of Representative Characteristics



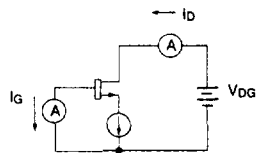
Forward transfer admittance vs. Drain current



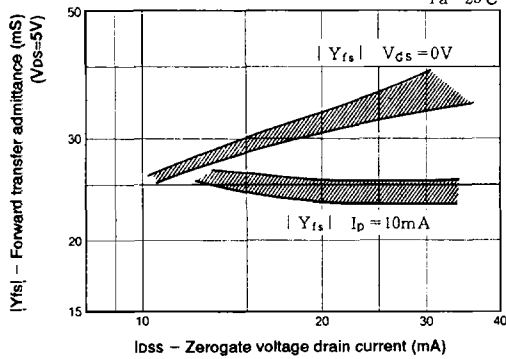
Gate cutoff vs. Supply voltage



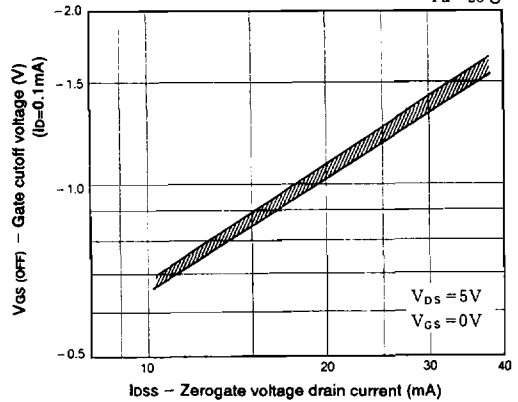
Ig Test Circuit



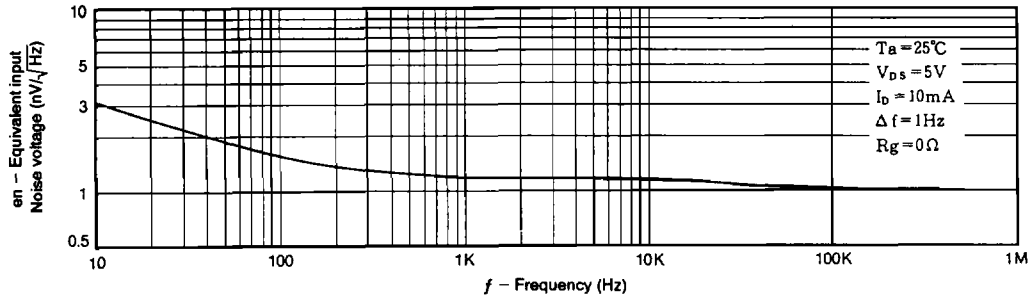
Forward transfer admittance vs. Zerogate voltage drain current



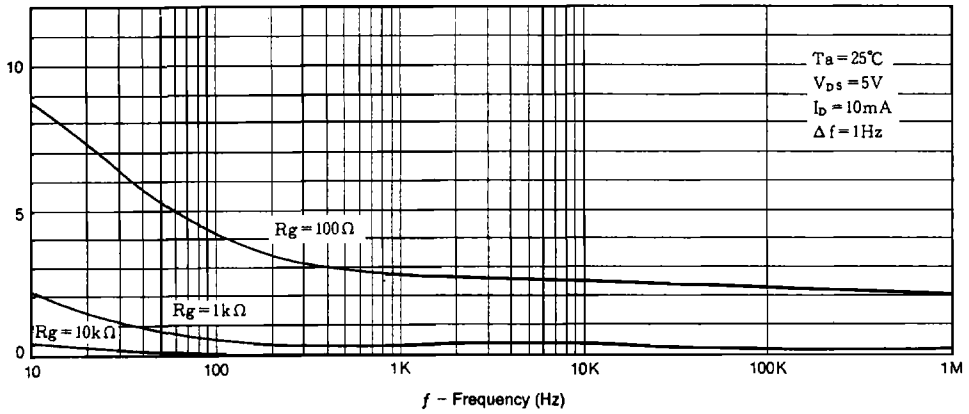
Gate cutoff voltage vs. Zerogate voltage drain current



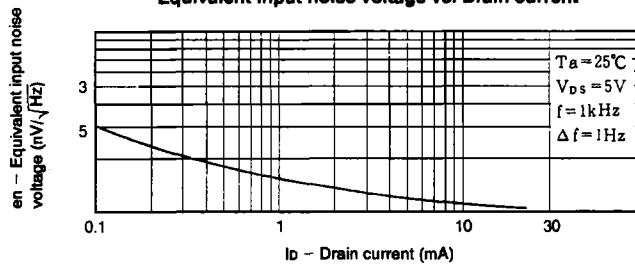
Equivalent input noise voltage vs. Frequency



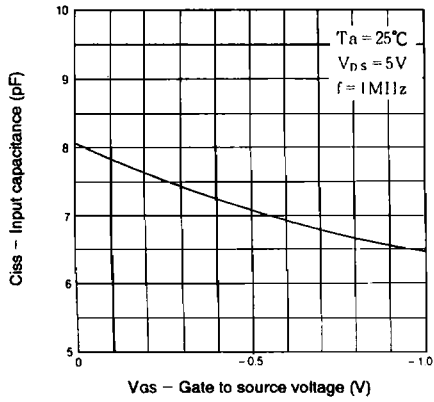
Noise figure vs. Frequency



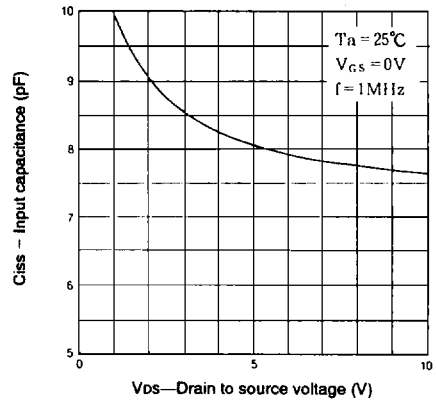
Equivalent input noise voltage vs. Drain current



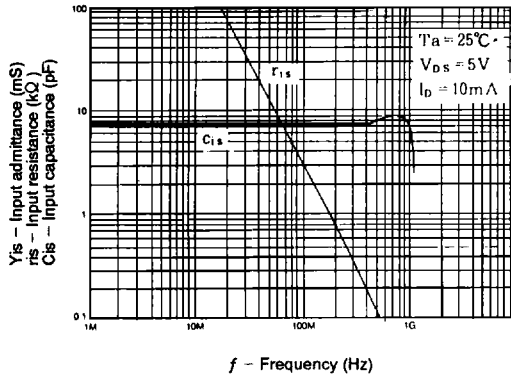
Input capacitance vs. Gate to source voltage



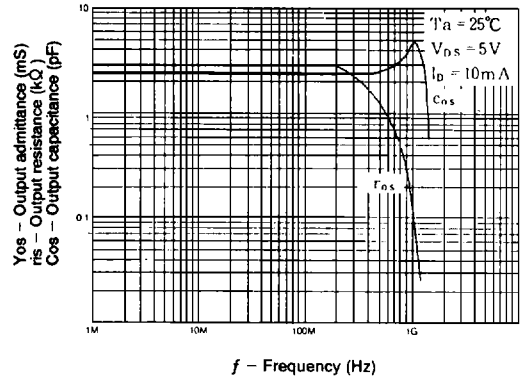
Input capacitance vs. Drain to source voltage



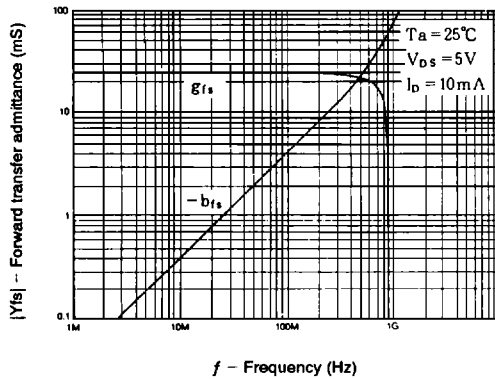
Input admittance vs. Frequency



Transfer characteristics vs. Ambient temperature



Forward transfer admittance vs. Frequency



Reverse transfer admittance vs. Frequency

